Plastic Power Transistors

NPN Silicon DPAK For Surface Mount Applications

Designed for high-gain audio amplifier applications.

Features

• High DC Current Gain -

$$h_{FE} = 120 \text{ (Min)} @ I_C = 500 \text{ mA}$$

= 40 (Min) @ $I_C = 2 \text{ A}$

• Low Collector-Emitter Saturation Voltage -

$$V_{CE(sat)} = 0.3 \text{ Vdc (Max)} @ I_C = 1 \text{ A}$$

• High Current-Gain - Bandwidth Product -

$$f_T = 65 \text{ MHz (Min)} @ I_C = 100 \text{ mA}$$

- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings:
 - Human Body Model, 3B > 8000 V
 - Machine Model, C > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Packages*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CB}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current Continuous Peak	I _C	2 3	Adc
Base Current	Ι _Β	0.4	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 0.1	W W/°C
Total Device Dissipation @ T _A = 25°C* Derate above 25°C	P _D	1.68 0.011	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +175	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

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SILICON POWER TRANSISTORS 2 AMPERES 50 VOLTS 15 WATTS



DPAK CASE 369C STYLE 1

MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Device

ORDERING INFORMATION

Device	Package	Shipping [†]
NJD2873T4G	DPAK (Pb-Free)	2,500 Units / Reel
NJVNJD2873T4G	DPAK (Pb-Free)	2,500 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 1)	$egin{array}{c} {\sf R}_{ heta {\sf JC}} \ {\sf R}_{ heta {\sf JA}} \end{array}$	10 89.3	°C/W

^{1.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	- Cymbol		шил	J.III
OFF CHARACTERISTICS	<u> </u>	1	<u> </u>	
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	50	-	Vdc
Collector Cutoff Current (V _{CB} = 50 Vdc, I _E = 0)	I _{CBO}	-	100	nAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	-	100	nAdc
ON CHARACTERISTICS				
DC Current Gain (Note 2) $ \begin{aligned} &(I_C = 0.5 \text{ A, } V_{CE} = 2 \text{ V}) \\ &(I_C = 2 \text{ Adc, } V_{CE} = 2 \text{ Vdc}) \\ &(I_C = 0.75 \text{ Adc, } V_{CE} = 1.6 \text{ Vdc, } -40^{\circ}\text{C} \leq T_J \leq 150^{\circ}\text{C}) \end{aligned} $	h _{FE}	120 40 80	360 - 360	I
Collector–Emitter Saturation Voltage (Note 2) (I _C = 1 A, I _B = 0.05 A)	V _{CE(sat)}	-	0.3	Vdc
Base-Emitter Saturation Voltage (Note 2) (I _C = 1 A, I _B = 0.05 Adc)	V _{BE(sat)}	-	1.2	Vdc
Base–Emitter On Voltage (Note 2) $ (I_C = 1 \text{ Adc, } V_{CE} = 2 \text{ Vdc}) $ $ (I_C = 0.75 \text{ Adc, } V_{CE} = 1.6 \text{ Vdc, } -40^{\circ}\text{C} \leq T_J \leq 150^{\circ}\text{C}) $	V _{BE(on)}	- -	1.2 0.95	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain - Bandwidth Product (Note 3) (I _C = 100 mAdc, V _{CE} = 10 Vdc, f _{test} = 10 MHz)	f _T	65	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)	C _{ob}	-	80	pF

^{2.} Pulse Test: Pulse Width = 300 $\mu s,$ Duty Cycle \approx 2%. 3. $f_T=\left|h_{fe}\right| \bullet f_{test}.$

TYPICAL CHARACTERISTICS

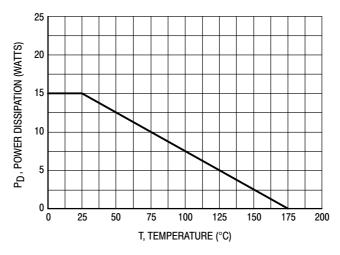


Figure 1. Power Derating

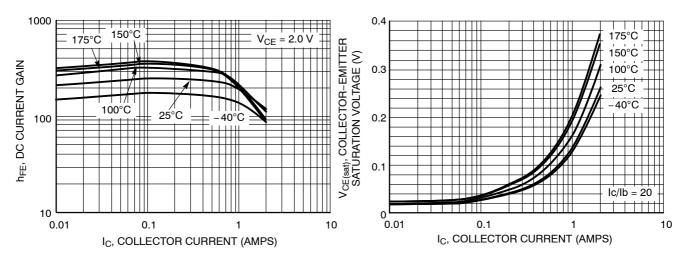


Figure 2. DC Current Gain

Figure 3. Collector-Emitter Saturation Voltage

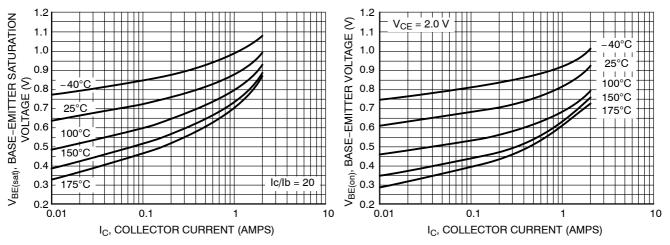


Figure 4. Base-Emitter Saturation Voltage

Figure 5. Base-Emitter Voltage

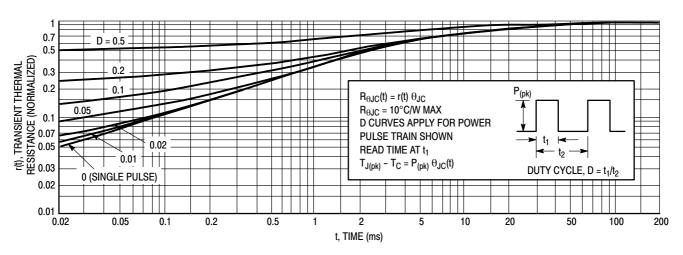
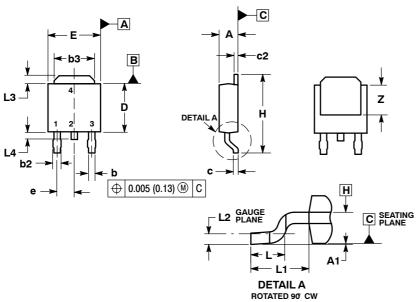
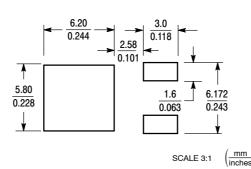


Figure 6. Thermal Response

PACKAGE DIMENSIONS

DPAK CASE 369C-01 ISSUE D





SOLDERING FOOTPRINT*

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: INCHES.
 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.

 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL
- NOT EXCEED 0.006 INCHES PER SIDE.

 5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020	BSC	0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

STYLE 1:

- PIN 1. BASE
 - 2. COLLECTOR
 - EMITTER
 - COLLECTOR

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